

INCHANGE Semiconductor

isc Product Specification

isc Silicon NPN Power Transistor

2SC5249

DESCRIPTION

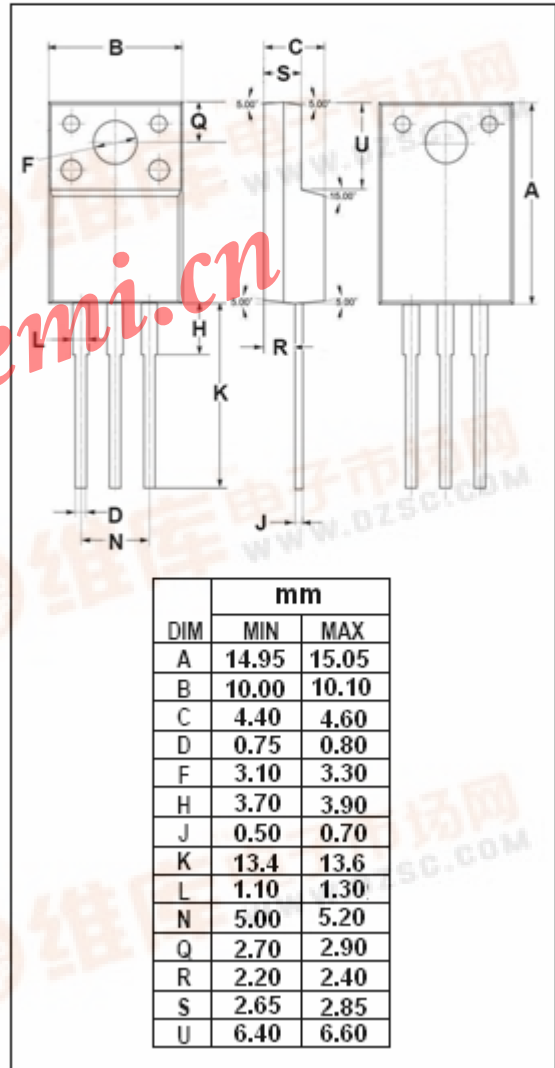
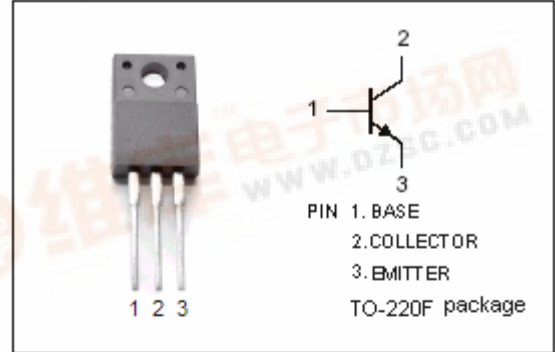
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 600V(\text{Min})$
- High Switching Speed

APPLICATIONS

- Designed for switching regulator and general purpose applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	600	V
$V_{CEO}$	Collector-Emitter Voltage	600	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	3	A
$I_{CM}$	Collector Current-Peak	6	A
$I_B$	Base Current-Continuous	1.5	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	35	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



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## ELECTRICAL CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA ; I <sub>B</sub> = 0	600			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.2A			0.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.2A			1.2	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 600V ; I <sub>E</sub> = 0			100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			100	μ A
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 4V	20		40	
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1MHz		50		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>E</sub> = -0.3A ; V <sub>CE</sub> = 12V		6		MHz

## Switching Times

t <sub>on</sub>	Turn-On Time	I <sub>C</sub> = 1A; I <sub>B1</sub> = -I <sub>B2</sub> = 0.1A; V <sub>CC</sub> = 200V; R <sub>L</sub> = 200 Ω			1.0	μ s
t <sub>stg</sub>	Storage Time				19	μ s
t <sub>f</sub>	Fall Time				1.0	μ s